

Customer - invoice address: Brno University of Technology CEITEC - Central European Institute of Technology Purkyňova 123 612 00 Brno Czech Republic IN: 00216305 TAX: CZ00216305 Contact: Tel.: Fax: E-mail: @ceitec.vutbr.cz <u>Deliver goods to the address:</u> Brno University of Technology Středoevropský technologický institut Purkyňova 123 612 00 Brno	Vendor (no.SAP): 206953 SIEGERT WAFER GmbH Charlottenburger Allee 7 52068 Aachen Germany IN: TAX: DE815357871 Contact: Tel.: Fax: E-mail:
The number of this order, please always write to your invoice! Thank you.	

According to your quotation no.: 120155 we order following wafers and accept discount.

Delivery date: **26.07.2018**

Currency: **EUR**

Text of item	Quantity	Unit price exc. VAT	VAT rate	Total excl. VAT	Total incl. VAT
Sapphire wafer 4"/C-Plane/SSP	25,00 PC	52,00		1 300,00	
Sapphire wafer 4"/C-Plane/DSP	25,00 PC	58,00		1 450,00	
Fused Silica Wafer 4"/DSP/Ra<1nm	25,00 PC	31,00		775,00	
Si-Wafer 4P0/10-20/DSP/TTV<5	100,00 PC	16,90		1 690,00	
Si-Wafer 4N0/Ph/525/SSP/TTV<5	75,00 PC	12,20		915,00	
Si-Wafer 4N0/Ph/276/SSP/TTV<5	25,00 PC	14,80		370,00	
Si-Wafer 4P0/1-5/SSP/TTV<5	75,00 PC	12,20		915,00	
Si-Wafer 4"/intrinsic/<100>/DSP/TTV	25,00 PC	66,50		1 662,50	
Si-Wafer 4P1/5-10/SSP/TTV<5	38,00 PC	13,70		520,60	
Si-Wafer 8"/Dummy/600/SSP	25,00 PC	15,00		375,00	
Shipping	1,00 PC	45,00		45,00	
Total order value				10 018,10	

Date, name and signature - BUT

Vendor confirms the order, ie. customer made it through the draft contract accepts and agrees to abide by the content of contract.

Date, name and signature - vendor

In the case of payment in euro within the EU we send SEPA payments with the type of charge SHA / SLV according to EU regulation (no.) 260/2012.

Brno University of Technology as a public university was established by Act no. 111/1998 Coll. and is not registered in the commercial register.

SIEGERT WAFER GmbH, Charlottenburger Allee 7, 52068 Aachen, GERMANY

Brno University of Technology
Stredoevropsky technologicky institut
Purkynova 123
61200 Brno
CZECH REPUBLIC

Order Acknowledgement

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Order No. 3586202050	Our Reference 17946.vp	
SW Contact	Phone	
Customer No. 11286	VAT-ID CZ00216305	
Contact Person	Phone	
Email @ceitec.vutbr.cz		
Invoice Address Vysoké učení technické v Brne Antoninska 548/1 BRNO-STŘED, VEVEŘÍ 601 90 Brno CZECH REPUBLIC		

The detailed Specification can be found on the following page(s)

Currency: EUR

Description	Quantity	Unit	Price	Total
1 Sapphire Wafer 4"/C-Plane/650±25/SSP Lead Time: 1-2 weeks	25	pcs	52,00	1.300,00
2 Sapphire Wafer 4"/C-Plane/650±20/DSP Lead Time: 1-2 weeks	25	pcs	58,00	1.450,00
3 Fused Silica Wafer 4"/500±20/DSP/Ra<1nm Lead Time: 1-2 weeks alternative to item 3	25	pcs	31,00	775,00
4 Si-Wafer 4P0/10-20/525±20/DSP/TTV<5 Lead Time: 1-2 weeks	100	pcs	16,90	1.690,00
5 Si-Wafer 4N0/Ph/1-5/525±20/SSP/TTV<5 Lead Time: 1-2 weeks	75	pcs	12,20	915,00
6 Si-Wafer 4N0/Ph/1-5/275±20/SSP/TTV<5 Lead Time: 1-2 weeks	25	pcs	14,80	370,00
7 Si-Wafer 4P0/1-5/525±20/SSP/TTV<5 Lead Time: 1-2 weeks	75	pcs	12,20	915,00
8 Si-Wafer 4"/intrinsic/<100>/>10k/525±20/DSP/TTV<5 Lead Time: 1-2 weeks	25	pcs	66,50	1.662,50
9 Si-Wafer 4P1/5-10/525±20/SSP/TTV<5 Lead Time: 1-2 weeks	38	pcs	13,70	520,60
10 Si-Wafer 8"/Dummy/>600/SSP Lead Time: 1-2 weeks price including cleanroom fee for separating the wafers	25	pcs	15,00	375,00
11 Shipping and Packaging (Europe)	1	pc	45,00	45,00

If all items are ordered we grant a discount of 5%!



SIEGERT WAFER GmbH
Charlottenburger Allee 7
52068 Aachen, GERMANY

General Manager:
Dipl.-Ing. Marcus Siegert, Michael Kinch

Phone +49 241 900 5333
Fax +49 241 9161 3387
Email info@siegertwafer.de
VAT-ID DE815357871
Register HRB 17499

Bank Name
Account
Bank Code
Swift/BIC
IBAN



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Subtotal before Discount	10.018,10
	- 500,91
Subtotal	9.517,19
Net Amount	9.517,19
Total (EUR)	9.517,19

Our Standard Terms and Conditions of Sale and Delivery apply, accessible at www.terms.siegertwafer.com

We will be glad to provide you with a printed version upon request

INCOTERMS	Payment Terms
EXW-Aachen-GER	21 days net

Remarks

- Please always state our reference number on all documents and in all e-mails: 17946.vp
- Apparent defects must be reported in writing within a period of 5 days from receipt of the goods (Standard Terms and Conditions, clause 8.3)

Thank you for your order!



SIEGERT WAFER GmbH
Charlottenburger Allee 7
52068 Aachen, GERMANY

General Manager:
Dipl.-Ing. Marcus Siegert, Michael Kinch

Phone +49 241 900 5333
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Email info@siegertwafer.de
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Register HRB 17499

Bank Name
Account
Bank Code
Swift/BIC
IBAN



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Item	Specification
1	<p>Diameter: 100 ±0.2 mm</p> <p>Material: Al₂O₃</p> <p>Growth: Kyropolos</p> <p>Purity: 99.998 %</p> <p>Orientation: C-Plane (0001) ON ±0.3°</p> <p>Thickness: 650 ±25 µm</p> <p>Frontside Finish: Polished (Ra<=0.3 nm)</p> <p>Backside Finish: As Lapped (Ra<1.2 µm)</p> <p>Flats: 1 Primary Flat</p> <p>Primary Flat Length: 32 ±1mm</p> <p>Primary Flat Location: Parallel to the A-axis <11-20> ±0.5°</p> <p>Lasermark: None</p> <p>TTV: <10 µm</p> <p>Bow: <15 µm</p> <p>Edge Profile: Ground, none polished</p> <p>Cleanliness: CRC 100</p> <p>Packaging: Standard Cassettes</p>
2	<p>Diameter: 100 ±0.25 mm</p> <p>Material: Al₂O₃</p> <p>Growth: Kyropolos</p> <p>Purity: 99.998 %</p> <p>Orientation: C-Plane (0001) ON ±0.2°</p> <p>Thickness: 650 ±20 µm</p> <p>Frontside Finish: Polished (Ra<=0.3 nm)</p> <p>Backside Finish: Polished (Ra<=0.3 nm)</p> <p>Flats: 1 Primary Flat</p> <p>Primary Flat Length: 32 ±1 mm</p> <p>Primary Flat Location: @ (11-20) ±0.5° (A-Plane)</p> <p>Lasermark: None</p> <p>TTV: <10 µm</p> <p>Bow: <15 µm</p> <p>Edge Profile: Ground, none polished</p> <p>Cleanliness: CRC 100</p> <p>Packaging: Standard cassettes, sealed in bags</p>
3	<p>Diameter: 100 ±0.5 mm</p> <p>Material: Fused Silica, UV-Grade</p> <p>Thickness: 500 ±20 µm</p> <p>Surface Finish: Double Side Polished</p> <p>Surface Quality (S/D): 20/10</p> <p>Surface Roughness: Ra<1 nm</p> <p>Flats: 1 Primary Flat, SEMI-Std.</p> <p>TTV: <10 µm</p> <p>Bow: <30 µm</p> <p>Edge Profile: Ground, C-shaped</p> <p>Cleanliness: Pre-Cleaned, Optical Standard</p> <p>Packaging: Standard Cassettes</p>
4	<p>Diameter: 100 ±0.3 mm</p> <p>Material: Silicon</p> <p>Growth: CZ</p> <p>Grade: Prime</p> <p>Type/Dopant: P/B</p> <p>Orientation: <100> ±0.5°</p> <p>Resistivity: 10-20 Ohm-cm</p> <p>Thickness: 525 ±20 µm</p>





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Item	Specification
	Surface Finish: Double Side Polished Flats: 2, SEMI-Std. TTV: <5 µm Bow: <30 µm Warp: <30 µm Particles ≥0.2 µm: <20 Particles ≥0.3 µm: <10 Packaging: Standard Cassettes
5	Diameter: 100 ±0.3 mm Material: Silicon Growth: CZ Grade: Prime Type/Dopant: N/Ph Orientation: <100> ±0.5° Resistivity: 1-5 Ohm-cm Thickness: 525 ±20 µm Surface Finish: Single Side Polished Flats: 2, SEMI-Std. TTV: <5 µm Bow: <30 µm Warp: <30 µm Particles ≥0.2 µm: <20 Particles ≥0.3 µm: <10 Packaging: Standard Cassettes
6	Diameter: 100 ±0.3 mm Material: Silicon Growth: CZ Grade: Prime Type/Dopant: N/Ph Orientation: <100> ±0.5° Resistivity: 1-5 Ohm-cm Thickness: 275 ±20 µm Surface Finish: Single Side Polished Flats: 2, SEMI-Std. TTV: <5 µm Bow: <30 µm Warp: <30 µm Particles ≥0.2 µm: <20 Particles ≥0.3 µm: <10 Packaging: Standard Cassettes
7	Diameter: 100 ±0.3 mm Material: Silicon Growth: CZ Grade: Prime Type/Dopant: P/B Orientation: <100> ±0.5° Resistivity: 1-5 Ohm-cm Thickness: 525 ±20 µm Surface Finish: Single Side Polished Flats: 2, SEMI-Std. Lasermark: None TTV: <5 µm Bow: <30 µm Warp: <30 µm





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Item	Specification
	Particles $\geq 0.3 \mu\text{m}$: <10 Packaging: Cassettes
8	Diameter: 100 ± 0.3 mm Material: Silicon Growth: FZ Grade: Prime Type/Dopant: Intrinsic/Undoped Orientation: $\langle 100 \rangle \pm 0.5^\circ$ Resistivity: $> 10,000 \text{ Ohm-cm}$ Thickness: $525 \pm 20 \mu\text{m}$ Surface Finish: Double Side Polished Flats: 2, SEMI-Std. Secondary Flat Location: 180° from Primary Flat TTV: $< 5 \mu\text{m}$ Bow: $< 30 \mu\text{m}$ Warp: $< 30 \mu\text{m}$ Particles $\geq 0.2 \mu\text{m}$: < 20 Particles $\geq 0.3 \mu\text{m}$: < 10 Packaging: Standard Cassette
9	Diameter: 100 ± 0.3 mm Material: Silicon Growth: CZ Grade: Prime Type/Dopant: P/B Orientation: $\langle 111 \rangle \text{ ON } \pm 0.5^\circ$ Resistivity: $5-10 \text{ Ohm-cm}$ Thickness: $525 \pm 20 \mu\text{m}$ Surface Finish: Single Side Polished Flats: 1, SEMI-Std. TTV: $< 5 \mu\text{m}$ Bow: $< 30 \mu\text{m}$ Warp: $< 30 \mu\text{m}$ Particles $\geq 0.3 \mu\text{m}$: < 10 Packaging: Standard Cassettes
10	Diameter: 200 ± 0.3 mm Material: Silicon Growth: CZ Grade: Dummy Thickness: $> 600 \mu\text{m}$ Surface Finish: Single Side Polished Packaging: Standard Cassette

